

RF POWER MOSFET

N-Channel Enhancement Mode

DESCRIPTION:

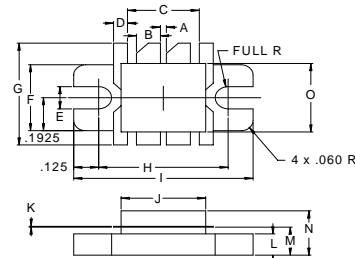
The **ASI BLF245C** is a VDMOS transistor designed for large signal amplifier applications in the VHF frequency range.

FEATURES INCLUDE:

- $P_G = 16$ dB Typical at 175 MHz
- **30:1** Load VSWR Capability
- **Omnigold™** metalization system

MAXIMUM RATINGS

I_D	6.0 A
V_{DS}	65 V
V_{GS}	± 20 V
P_{DISS}	68 W @ $T_C = 25$ °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.8 °C/W

PACKAGE STYLE .400 8L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.030 / 0.76
B	.115 / 2.92	.125 / 3.18
C		.360 / 9.14
D	.065 / 1.65	.075 / 1.91
E		.130 / 3.30
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

COMMON SOURCE

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_D = 10$ mA	65			V
I_{DSS}	$V_{DS} = 28$ V $V_{GS} = 0$ V			2.0	mA
I_{GSS}	$V_{DS} = 0$ V $V_{GS} = \pm 20$ V			1.0	μ A
$V_{GS(th)}$	$V_{DS} = 10$ V $I_D = 10$ mA	2.0		4.5	V
g_{fs}	$V_{DS} = 10$ V $I_D = 1.5$ A	1.2	1.9		S
C_{iss} C_{oss} C_{rss}	$V_{DS} = 28$ V $V_{GS} = 0$ V $f = 1.0$ MHz		125 75 7.0		pF
P_G η_D	$V_{DS} = 28$ V $I_{DQ} = 25$ mA $P_{out} = 30$ W $f = 150$ MHz	13 50	16 60		dB %
ψ	$V_{SWR} = 30:1$ AT ALL PHASE ANGLES	NO DEGRADATION IN OUTPUT POWER			